



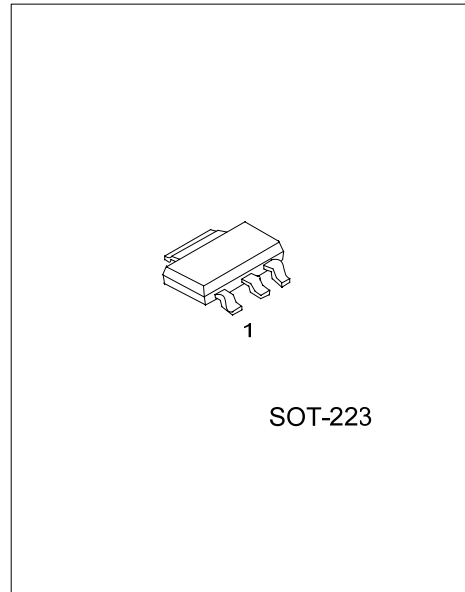
PZT5551

NPN SILICON TRANSISTOR

HIGH VOLTAGE SWITCHING TRANSISTOR

■ FEATURES

- * High Collector-Emitter Voltage:
V_{CEO}=160V
- *High current gain



*Pb-free plating product number:PZT5551L

■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
PZT5551-x-AA3-F-R	PZT5551L-x-AA3-F-R	SOT-223	B	C	E	Tape Reel

<p>PZT5551L-x-AA3-F-R</p>	<ul style="list-style-type: none"> (1)Packing Type (2)Pin Assignment (3)Package Type (4)Rank (5)Lead Plating 	<ul style="list-style-type: none"> (1) R: Tape Reel (2) refer to Pin Assignment (3) AA3: SOT-223 (4) x: refer to Classification of h_{FE} (5) L: Lead Free Plating, Blank: Pb/Sn
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■ ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6	V
DC Collector Current	I _C	600	mA
Power Dissipation	P _C	2	W
Operating Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-65 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance	θ _{JA}	62.5	°C/W

■ ELECTRICAL CHARACTERISTICS (Ta= 25°C, unless otherwise specified)

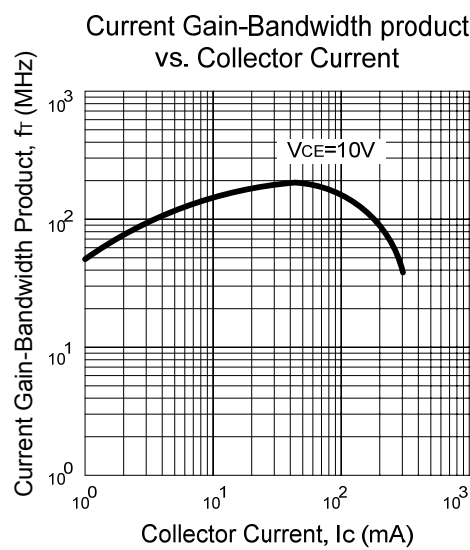
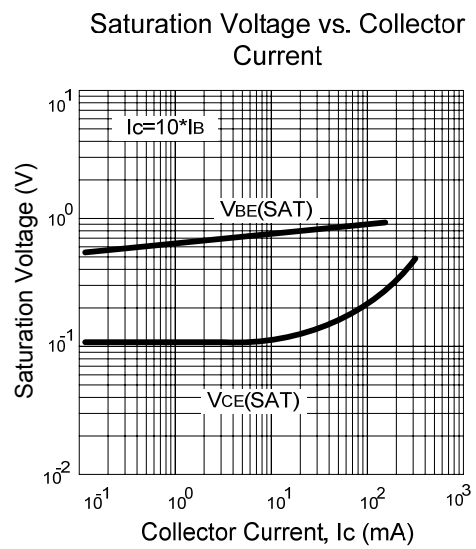
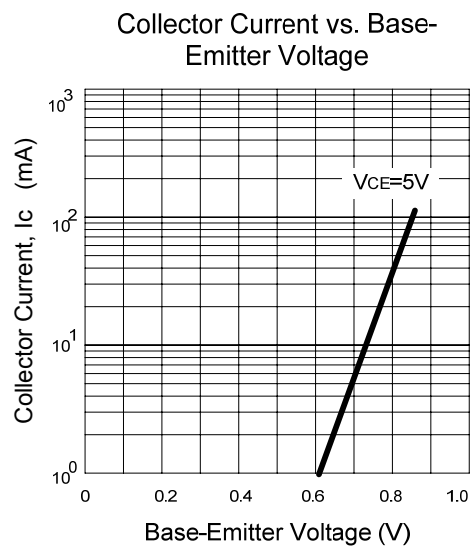
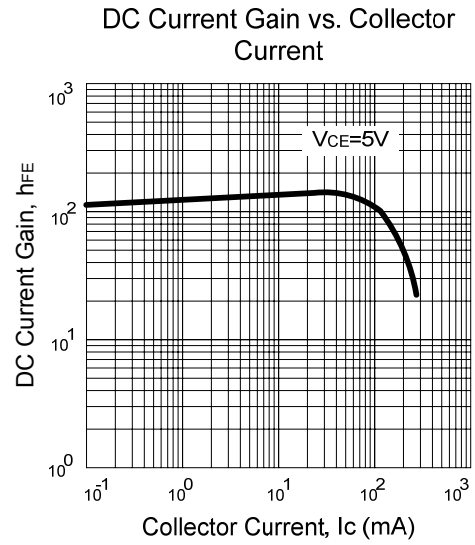
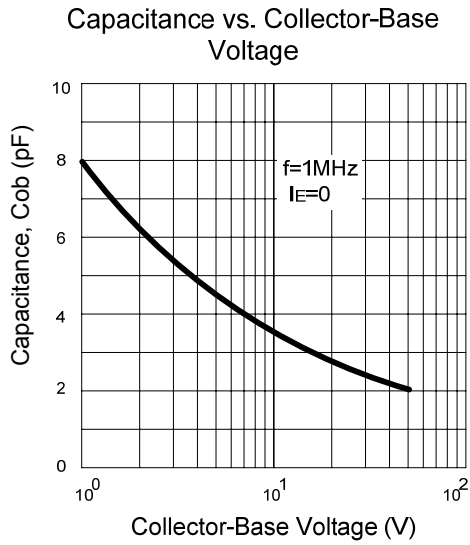
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =100μA, I _E =0	180			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	160			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =10μA, I _C =0	6			V
Collector Cut-off Current	I _{CBO}	V _{CB} =120V, I _E =0			50	nA
Emitter Cut-off Current	I _{EBO}	V _{BE} =4V, I _C =0			50	nA
DC Current Gain(note)	h _{FE}	V _{CE} =5V, I _C =1mA	80	160	400	
		V _{CE} =5V, I _C =10mA	80			
		V _{CE} =5V, I _C =50mA	80			
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =10mA, I _B =1mA			0.15	V
		I _C =50mA, I _B =5mA			0.2	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =10mA, I _B =1mA			1	V
		I _C =50mA, I _B =5mA			1	
Current Gain Bandwidth Product	f _T	V _{CE} =10V, I _C =10mA, f=100MHz	100		300	MHz
Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			6.0	pF
Noise Figure	NF	I _C =0.25mA, V _{CE} =5V R _S =1kΩ, f=10Hz ~ 15.7kHz			8	dB

Note: Pulse test: PW<300μs, Duty Cycle<2%

■ CLASSIFICATION OF h_{FE}

RANK	A	B	C
RANGE	80-170	150-240	200-400

TYPICAL CHARACTERISTICS



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